

GCU08AA-130HIGH POWER INVERTER USE
PRESS PACK TYPE**GCU08AA-130**

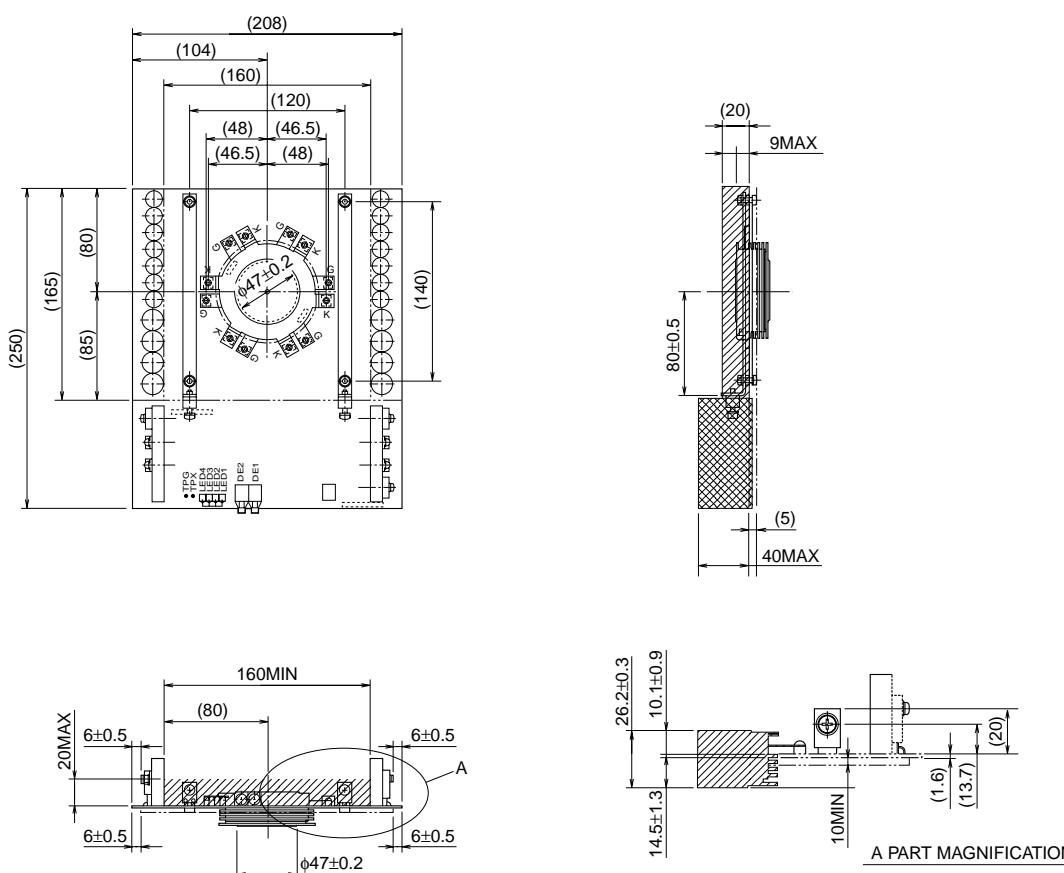
- Symmetrical GCT
- GCT and Gate driver are connected
- ITQRM Repetitive controllable on-state current 800A
- IT(AV) Average on-state current 330A
- VDRM Repetitive peak off-state voltage 6500V

APPLICATION

Inverters, DC choppers, Induction heaters, DC to DC converters.

OUTLINE DRAWING

Dimensions in mm



MITSUBISHI GATE COMMUTATED TURN-OFF THYRISTOR UNIT

GCU08AA-130

**HIGH POWER INVERTER USE
PRESS PACK TYPE**

GCT PART (Type name : FGC800A-130DS)

MAXIMUM RATINGS

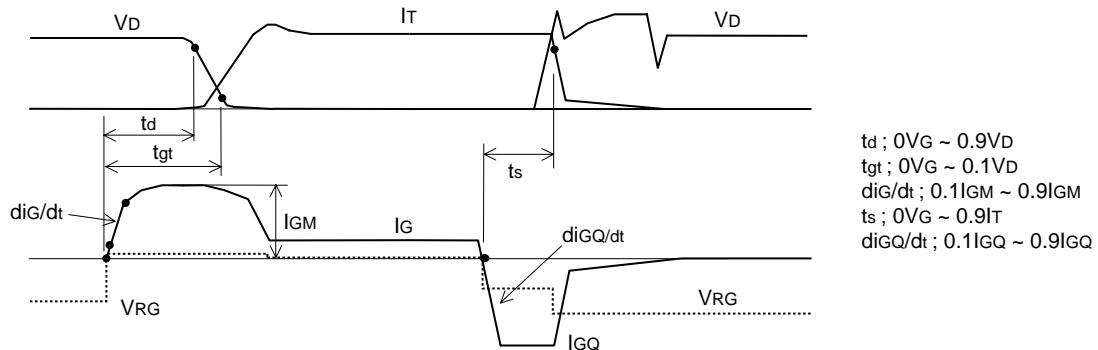
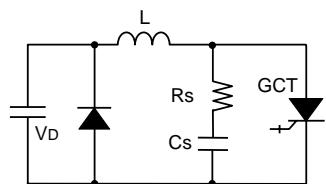
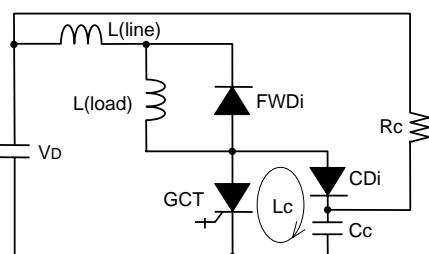
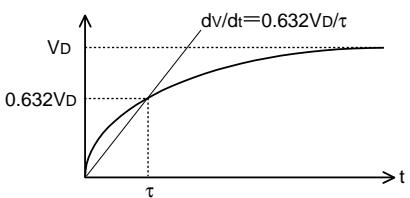
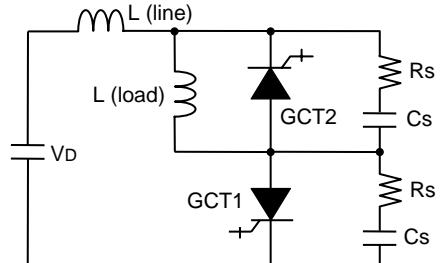
Symbol	Parameter	Conditions	Voltage class	Unit
V _{RRM}	Repetitive peak reverse voltage	—	6500	V
V _{RSM}	Non-repetitive peak reverse voltage	—	6500	V
V _{DRM}	Repetitive peak off-state voltage	V _{GK} = -2V	6500	V
V _{DSD}	Non-repetitive peak off-state voltage	V _{GK} = -2V	6500	V
V _{LTDs}	Long term DC stability voltage	V _{GK} = -2V, $\lambda = 100$ Fit	3600	V

Symbol	Parameter	Conditions	Ratings	Unit
I _{TQRM}	Repetitive controllable on-state current	V _{DM} = 3/4 V _{DRM} , V _D = 3000V, L _C = 0.3μH, VRG = 20V T _j = 25/115°C, With GU-D08 (see Fig. 1, 3)	800	A
I _{T(RMS)}	RMS on-state current	Applied for all conduction angles	520	A
I _{T(AV)}	Average on-state current	f = 60Hz, sinewave θ = 180°, T _f = 55°C	330	A
I _{TSM}	Surge on-state current		4.8	kA
I ² t	Current-squared, time integration	One half cycle at 60Hz, T _j = 115°C Start	9.6 × 10 ⁴	A ² s
dI/dt	Critical rate of rise of on-state current	V _D = 3000V, I _T = 800A, C _S = 0.1μF, R _S = 10Ω T _j = 25/115°C, f = 60Hz, With GU-D08 (see Fig. 1, 2)	1000	A/μs
V _{FGM}	Peak forward gate voltage		10	V
V _{RGM}	Peak reverse gate voltage		21	V
I _{FGM}	Peak forward gate current		500	A
I _{RGm}	Peak reverse gate current		800	A
P _{PGM}	Peak forward gate power dissipation		5	kW
P _{PRGM}	Peak reverse gate power dissipation		17	kW
P _{PG(AV)}	Average forward gate power dissipation		100	W
P _{PRG(AV)}	Average reverse gate power dissipation		120	W
T _j	Junction temperature		-20 ~ +115	°C
T _{stg}	Storage temperature		-20 ~ +150	°C
—	Mounting force required	(Recommended value 13kN)	11.1 ~ 15.8	kN
—	Weight	Typical value	530	g

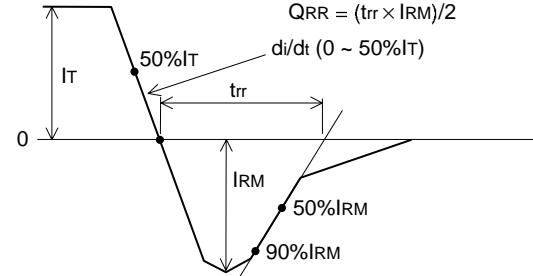
ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
V _{TM}	On-state voltage	I _T = 800A, T _j = 115°C	—	—	6.8	V
I _{RRM}	Repetitive peak reverse current	V _{RM} = 6500V, T _j = 115°C	—	—	150	mA
I _{DRM}	Repetitive peak off-state current	V _{DM} = 6500V, V _{GK} = -2V, T _j = 115°C	—	—	100	mA
I _{GRM}	Reverse gate current	VRG = 21V, T _j = 115°C	—	—	50	mA
dV/dt	Critical rate of rise of off-state voltage	V _D = 3000V, V _{GK} = -2V, T _j = 115°C (Expo. wave) (see Fig. 4)	3000	—	—	V/μs
t _{gt}	Turn-on time	I _T = 800A, V _D = 3000V, dI/dt = 1000A/μs, T _j = 115°C	—	—	5.0	μs
t _d	Delay time	C _S = 0.1μF, R _S = 10Ω	—	—	1.0	μs
E _{on}	Turn-on switching energy	With GU-D08 (see Fig. 1, 2)	—	—	1.6	J/P
t _s	Storage time	I _T = 800A, V _{DM} = 3/4 V _{DRM} , V _D = 3000V C _S = 0.1μF, R _S = 10Ω, VRG = 20V, T _j = 115°C	—	—	3.0	μs
E _{off}	Turn-off switching energy	With GU-D08 (see Fig. 1, 5)	—	—	6.0	J/P
Q _{RR}	Reverse recovery charge	V _R = 3000V, I _T = 800A, dI/dt = 1000A/μs	—	—	1650	μC
E _{rec}	Reverse recovery energy	C _S = 0.1μF, R _S = 10Ω, T _j = 115°C (see Fig. 5, 6)	—	—	5.0	J/P
I _{GT}	Gate trigger current	DC METHOD : V _D = 24V, R _L = 0.1Ω, T _j = 25°C	—	—	0.5	A
V _{GT}	Gate trigger voltage		—	—	1.5	V
R _{th(j-f)}	Thermal resistance	Junction to fin	—	—	0.025	°C/W

Mar. 2001

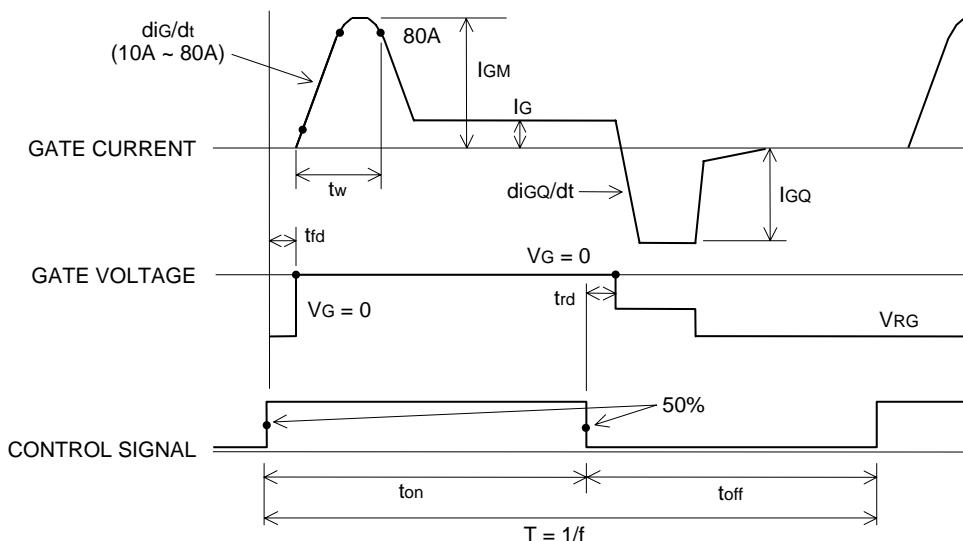
Fig. 1 Turn-on and Turn-off waveform**Fig. 2 Turn-on test circuit****Fig. 3 Turn-off test circuit
(With clamp circuit)****Fig. 4 dv/dt test waveform****Fig. 5 Turn-off and Recovery test circuit**

GCT1 : For turn-off test
GCT2 : For Recovery test

Fig. 6 Reverse recovery waveform

GATE DRIVER PART (Type name : GU-D08)

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
VC	Power supply (Note 1)	DC power supply	19	20	21	V
P	Power consumption (Note 2)	—	2.5	—	—	W
		IT = 330A, f = 780Hz	—	—	35	
—	Control signal (Note 3)	Optical fiber data link Transmitter : HFBR-1521 (HP) Receiver : HFBR-2521 (HP)	—	—	—	—
f	Frequency	IT = 330A, Duty 33%	—	—	780	Hz
tfd	Delay time of on gate current		—	—	3.0	μs
trd	Delay time of off gate current		—	—	3.0	μs
dig/dt	Critical rate of rise of on gate current		50	—	—	A/μs
IGM	Peak on gate current		—	90	—	A
tw	Width of on high gate current		3	—	—	μs
IG	On gate current	T _j ≥ -10°C	1.25	—	—	A
digQ/dt	Critical rate of rise of off gate current	VRG= 20V	—	1200	—	A/μs
Dmax	Maximum duty		—	—	100	%
Ta	Temperature	Operation temperature (Recommend : ≤ 40°C)	-10	—	+60	°C
—	Status signal (Note 4)		—	—	—	—

Fig. 7 Gate current, gate voltage and control signal waveform

Note 1. (1) Guaranteed power supply voltage for operation is 19V minimum and 21V maximum.

(2) When over voltage occurs, GDU voltage bus (G-K voltage for GCT) is clamped to be 21V if maximum voltage for input gate voltage from power supply is 25V and maximum duration of over voltage higher than 21V from power supply is 0.4 sec when control signal is on (Please see Fig. 8).

(3) When over voltage occurs, GDU voltage bus is clamped to be 21V with no time limitation if maximum voltage from power supply is 25V and control signal is off (Please see Fig. 8).

Note 2. GCT is off state and no gate signal is supplied for gate driver. No leakage current flows between gate and cathode of GCT.

Note 3. Optic fiber data link HFBR-1521 and HFBR-2521 are interlocked each other.

Note 4.

1. Status signal from LED**(1) Status signal**

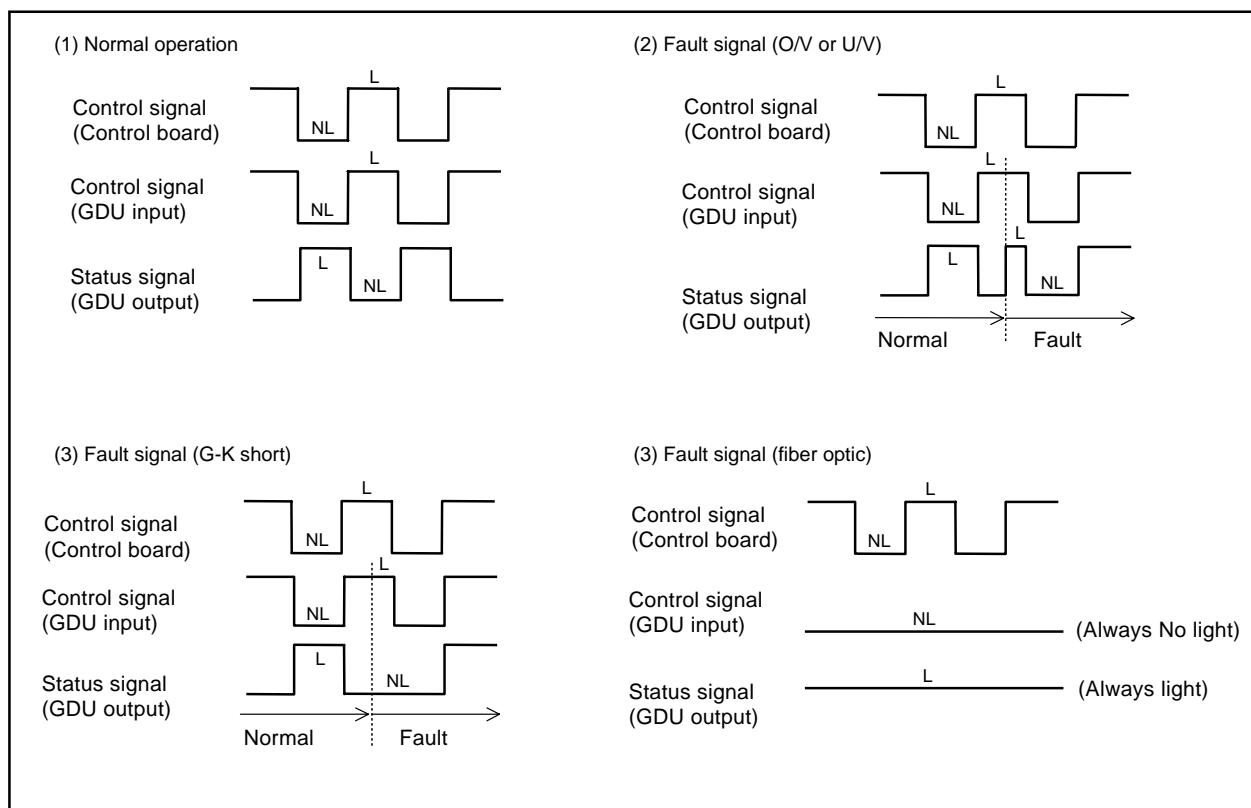
Status of GCT	LED 1 (Red)	LED 2 (Yellow)
On state	OFF	ON
Off state	ON	OFF

(2) Fault signal

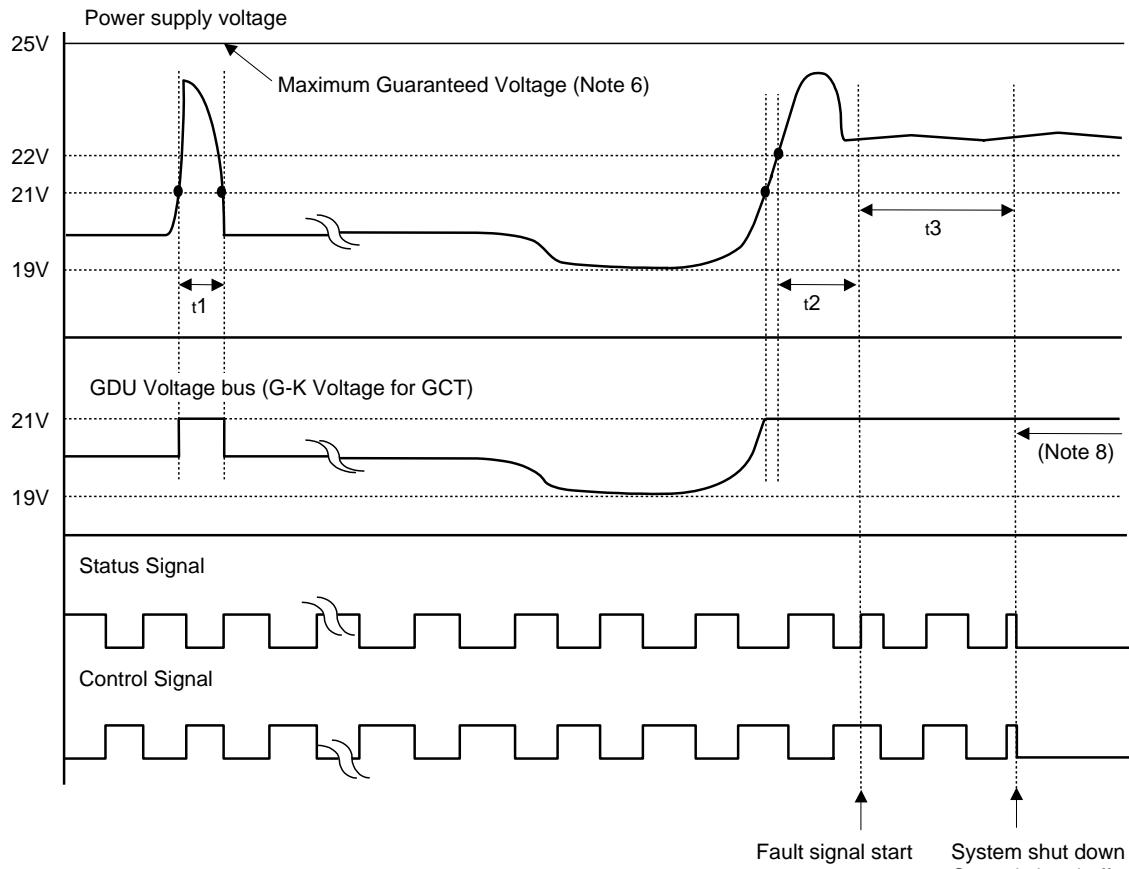
Status	G-K	PS	PS LED (LED 4)	G-K LED (LED 3)
Normal	Normal	20±1V	On	On
Fault	Normal	Voltage down	Off, V < 17.5V (Typ.)	Off (If V > 12.5V (Typ.) then LED 3 is on)
Fault	G-K short	20±1V	On	Off
Fault	G-K short	Voltage down	Off, V < 17.5V (Typ.)	Off

2. Status signal from Transmitter (Note 5)

(L : Light NL : No light)



Note 5. About over voltage fault signal, please see Fig. 8.

Fig. 8 Over voltage fault signal timing chart

- 1) t1 < 1.0ms (Max. repetition rate ; 1 pulse/100ms)
- 2) t2 ≥ 1.0ms
- 3) t3 < 0.4sec

Note 6. Maximum peak voltage of GDU input voltage from power supply should be lower than 25V.

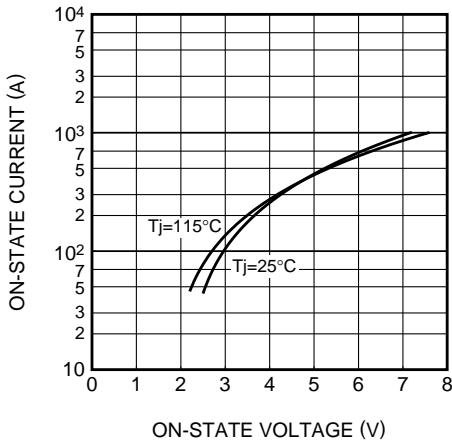
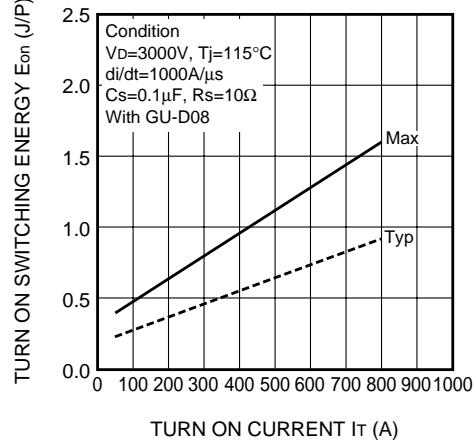
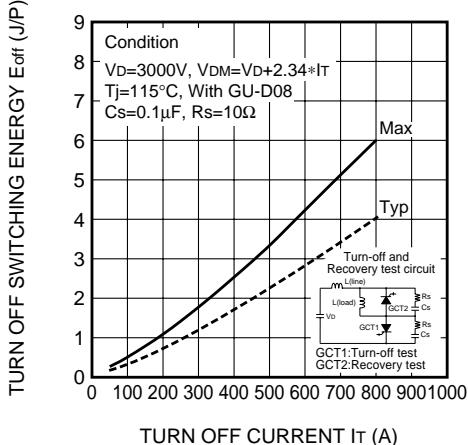
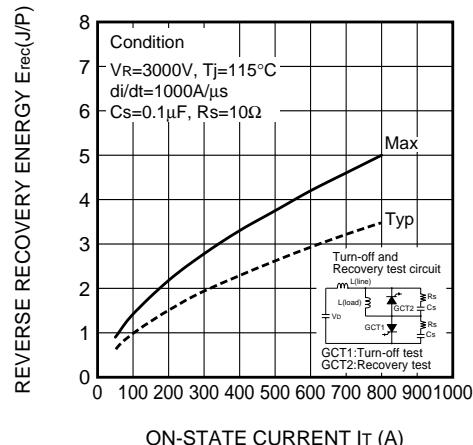
Note 7. If the period for over voltage < 1.0ms (period t1), no fault signal is sent.

If the period for over voltage ≥ 1.0ms, fault signal starts after period t2 from 22V of power supply voltage. System should be shut down (Control signal should be off) within period t3 from fault signal start.

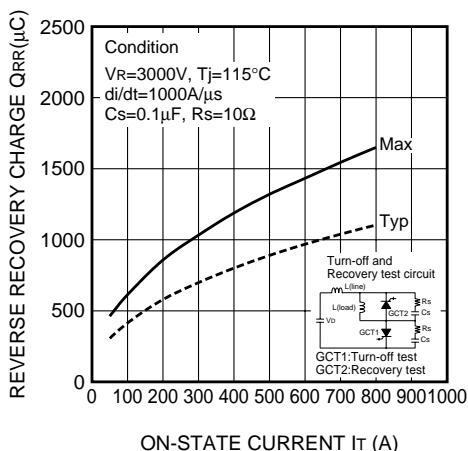
Note 8. GDU Voltage bus (G-K Voltage for GCT) is clamped to be 21V if power supply voltage is higher than 21V after system shut down (control signal off).

PERFORMANCE CURVES

MAXIMUM ON-STATE CHARACTERISTIC

E_{on} VS ITE_{off} VS ITE_{rec} VS IT

QRR VS IT

MAXIMUM THERMAL IMPEDANCE
CHARACTERISTIC
(JUNCTION TO FIN)